



APPLICATION DATA SHEET

Electronic Version v14

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Title of Invention	DEEP-TRENCH 1T-SRAM WITH BURIED OUT DIFFUSION WELL MERGED WITH AN ION IMPLANTATION WELL		
Application Type : regular, utility Attorney Docket Number : NAUP0547USA			
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Attorney Information: practitioner(s) at Customer Number: 027765  as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.			